

Brian Fluegel

List of Publications by Year in descending order

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29
papers

206
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1307594

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all docs

29
docs citations

29
times ranked

288
citing authors

#	ARTICLE	IF	CITATIONS
1	Photoluminescence up-conversion in GaAs/Al _x Ga _{1-x} As heterostructures. Physical Review B, 1998, 58, R4254-R4257.	3.2	42
2	Photoluminescence decay dynamics in an InGaN/AlGaIn/GaN double heterostructure blue-light emitting diode. Applied Physics Letters, 1995, 67, 1515-1517.	3.3	39
3	Electronic Raman scattering as an ultra-sensitive probe of strain effects in semiconductors. Nature Communications, 2015, 6, 7136.	12.8	20
4	Charge transfer states and carrier generation in 1D organolead iodide semiconductors. Journal of Materials Chemistry A, 2021, 9, 14977-14990.	10.3	15
5	Triplet-pair spin signatures from macroscopically aligned heteroacenes in an oriented single crystal. Proceedings of the National Academy of Sciences of the United States of America, 2022, 119, .	7.1	14
6	Mysterious absence of pair luminescence in gallium phosphide bismide. Applied Physics Express, 2015, 8, 061202.	2.4	9
7	Spectrally resolved localized states in GaAs _{1-x} Bi _x . Japanese Journal of Applied Physics, 2017, 56, 035801.	1.5	9
8	Precise Determination of the Direct-Indirect Band Gap Energy Crossover Composition in Al _x Ga _{1-x} As. Applied Physics Express, 2013, 6, 071201.	2.4	7
9	Bismuth-induced Raman modes in GaP _{1-x} Bi _x . Japanese Journal of Applied Physics, 2016, 55, 108002.	1.5	7
10	Ultrafast nonlinear gain dynamics in semiconductor nanocrystals. Phase Transitions, 1999, 68, 59-94.	1.3	6
11	Probing carrier lifetimes at dislocations in epitaxial CdTe. Applied Physics Express, 2014, 7, 065503.	2.4	5
12	Ultra-low threshold polariton condensation. Optics Letters, 2017, 42, 1165.	3.3	5
13	Direct observation of the quantum fluctuation driven amplitude mode in a microcavity polariton condensate. Physical Review B, 2021, 103, .	3.2	4
14	Spectroscopic determination of the bandgap crossover composition in MBE-grown Al _x Ga _{1-x} As. Japanese Journal of Applied Physics, 2015, 54, 042402.	1.5	4
15	Investigation of effects of processing and impurities on the properties of CdTe using microscopic two-dimensional photoluminescence imaging technique. , 2009, , .		3
16	Eigenstate localization in an asymmetric coupled quantum well pair. Superlattices and Microstructures, 2012, 51, 834-841.	3.1	3
17	Carrier lifetime as a function of Se content for CdSe _{1-x} Te _x films grown on Al ₂ O ₃ and MgZnO. , 2021, , .		3
18	Femtosecond optical nonlinearities under resonant excitation of excitons in CdSe. Journal of Crystal Growth, 1992, 117, 768-772.	1.5	2

#	ARTICLE	IF	CITATIONS
19	Mechanism of asymmetric lineshape broadening in GaAs $\frac{1}{\omega} \frac{d\omega}{d\omega} \hat{\omega}$ $\frac{1}{\omega} \frac{d\omega}{d\omega} \hat{\omega}$ <i>Raman spectra. Physical Review B, 2012, 86, .</i>	4.2	2
20	Crystallographically aligned 1.508 eV nitrogen pairs in ultra-dilute GaAs:N. <i>Japanese Journal of Applied Physics</i> , 2018, 57, 090302.	1.5	2
21	Design and Demonstration of AlIn1-xP Multiple Quantum Well Light-Emitting Diodes. <i>Journal Physics D: Applied Physics</i> , 0, , .	2.8	2
22	Femtosecond hole-burning and nonlinear dynamics of quantum-confined semiconductor-doped glasses. , 1990, , .		1
23	Magnetic field-induced direct \leftrightarrow indirect crossover in Al _x Ga _{1-x} As. <i>Applied Physics Express</i> , 2014, 7, 111201.	2.4	1
24	Ferroelastic modulation and the Bloch formalism. <i>Science Advances</i> , 2017, 3, e1602754.	10.3	1
25	Femtosecond nonlinear optics of semiconductor quantum wells. , 1992, , .		0
26	Quantum dots in the strong confinement regime: a model system for gain in quasi-zero-dimensional semiconductors. , 1996, , .		0
27	Observation of spectral hole sidebands in the gain region of an inverted semiconductor. , 1996, , .		0
28	Consequences of spatial antisymmetry on light. , 2016, , .		0
29	Bismuth interstitial impurities and the optical properties of GaP $\frac{1}{\omega} \frac{d\omega}{d\omega} \hat{\omega}$ $\frac{1}{\omega} \frac{d\omega}{d\omega} \hat{\omega}$ <i>Japanese Journal of Applied Physics</i> , 2017, 56, 111201.	1.5	0